

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2340	alignment adj mark and etch\$4 with substrate	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/04/02 10:01
L2	356	alignment adj mark and etch\$4 with semiconductor with (oxide or nitride or dielectric or insulat\$4) with substrate	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/04/02 10:01
L3	138	alignment adj mark and etch\$4 with semiconductor with (oxide or nitride or dielectric or insulat\$4) with substrate same (expos\$3 with substrate)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/04/02 10:01
L4	34	L3 and stepper	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/04/02 10:01
L5	26	L3 and stepper and photoresist	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/04/02 10:01
L6	38	alignment adj mark and etch\$4 with SOI adj substrate	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/04/02 10:01

## EAST Search History

L7	18	L6 and alignment adj mark and etch\$4 with semiconductor with (oxide or nitride or dielectric or insulat\$4) with substrate	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2007/04/02 10:01
L8	18	L7 and (mask or photoresist or resist or photomask)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2007/04/02 10:01
L9	6	("5286673"   "5369050"   "6194287"   "6215197"   "6303460"   "6440816").PN.	US-PGPU B; USPAT; USOCR	OR	OFF	2007/04/02 10:01
L10	4	L9 and SOI	US-PGPU B; USPAT; USOCR	OR	OFF	2007/04/02 10:01
L11	9	deep adj alignment adj mark	US-PGPU B; USPAT; USOCR	OR	OFF	2007/04/02 10:01
L12	12	deep adj alignment adj mark	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/04/02 10:01
L13	1	L12 and SOI	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/04/02 10:01
L14	229	bulk adj substrate same (oxide or nitride or insulat\$3 or dielectric) same. semiconductor adj layer	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/04/02 10:01

## EAST Search History

L15	5	L14 and alignment adj mark	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/04/02 10:01
L16	930	438/200.ccls.	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/04/02 10:01
L17	502	438/427.ccls.	US-PGPU B; USPAT; USOCR	OR	OFF	2007/04/02 10:01
L18	1963	438/424.ccls.	US-PGPU B; USPAT; USOCR	OR	OFF	2007/04/02 10:01
L19	147	438/405.ccls.	US-PGPU B; USPAT; USOCR	OR	OFF	2007/04/02 10:01
L20	841	438/462.ccls.	US-PGPU B; USPAT; USOCR	OR	OFF	2007/04/02 10:01
L21	407	438/975.ccls.	US-PGPU B; USPAT; USOCR	OR	OFF	2007/04/02 10:01
L22	789	257/797.ccls.	US-PGPU B; USPAT; USOCR	OR	OFF	2007/04/02 10:01
L23	8	L16 and alignment adj mark	US-PGPU B; USPAT; USOCR	OR	OFF	2007/04/02 10:01
L24	24	L17 and alignment adj mark	US-PGPU B; USPAT; USOCR	OR	OFF	2007/04/02 10:01
L25	38	L18 and alignment adj mark	US-PGPU B; USPAT; USOCR	OR	OFF	2007/04/02 10:01

## EAST Search History

L26	2	L19 and alignment adj mark	US-PGPU B; USPAT; USOCR	OR	OFF	2007/04/02 10:01
L27	160	L20 and alignment adj mark	US-PGPU B; USPAT; USOCR	OR	OFF	2007/04/02 10:01
L28	160	L21 and alignment adj mark	US-PGPU B; USPAT; USOCR	OR	OFF	2007/04/02 10:01
L29	313	L22 and alignment adj mark	US-PGPU B; USPAT; USOCR	OR	OFF	2007/04/02 10:01
L30	3	L23 and substrate same (oxide or nitride or insulat\$3 or dielectric) same semiconductor adj layer	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/04/02 10:01
L31	1	L24 and substrate same (oxide or nitride or insulat\$3 or dielectric) same semiconductor adj layer	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/04/02 10:01
L32	3	L25 and substrate same (oxide or nitride or insulat\$3 or dielectric) same semiconductor adj layer	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/04/02 10:01
L33	0	L26 and substrate same (oxide or nitride or insulat\$3 or dielectric) same semiconductor adj layer	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/04/02 10:01

## EAST Search History

L34	5	L27 and substrate same (oxide or nitride or insulat\$3 or dielectric) same semiconductor adj layer	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/04/02 10:01
L35	11	L28 and substrate same (oxide or nitride or insulat\$3 or dielectric) same semiconductor adj layer	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/04/02 10:01
L36	9	L29 and substrate same (oxide or nitride or insulat\$3 or dielectric) same semiconductor adj layer	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/04/02 10:01
L37	129	L29 and etch\$3 with substrate	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/04/02 10:01
L38	3	L30 and etch\$3 with substrate	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/04/02 10:01
L39	1	L31 and etch\$3 with substrate	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/04/02 10:01

## EAST Search History

L40	3	L32 and etch\$3 with substrate	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/04/02 10:01
L41	0	L33 and etch\$3 with substrate	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/04/02 10:01
L42	4	L34 and etch\$3 with substrate	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/04/02 10:01
L43	9	L35 and etch\$3 with substrate	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/04/02 10:01
L44	7	L36 and etch\$3 with substrate	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/04/02 10:01
L45	7330	L1 L2 L3 L4 L5 L6 L7 L8 L9 L10 L11 L12 L13 L14 L15 L16 L17 L18 L19 L20 L21 L22 L23 L24 L25 L26 L27 L28 L29 L30 L31 L32 L33 L34 L35 L36 L37 L38 L39 L40 L41 L42 L43 L44	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2007/04/02 10:03

## EAST Search History

L46	0	buried adj alignment adj mark with wiithin with substrate	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2007/04/02 10:03
L47	0	alignment adj mark with wiithin with substrate	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2007/04/02 10:03

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S54	2246516	alignment adj mark with SOI substrate	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/22 13:46
S55	35	alignment adj mark with SOI adj substrate	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/22 15:54
S56	4	("5316966"   "5369050"   "5578519"   "5893744").PN.	US-PGPU B; USPAT; USOCR	OR	OFF	2006/08/22 15:24
S57	28	alignment adj mark with SOI adj substrate and etch\$3 with substrate	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/22 16:08
S58	5	alignment adj mark with bulk adj substrate	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/22 16:09



## EAST Search History

S59	802	Hause.in.	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/08/22 16:09
S60	80	Hause.in. and alignment	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/08/22 16:10
S61	58	Hause.in. and alignment and substrate	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/08/22 16:10
S62	3	Hause.in. and alignment adj mark and substrate	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/08/22 16:21
S63	1	Haines.in. and alignment adj mark and substrate	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/08/22 16:17

## EAST Search History

S64	0	Exterkamp.in. and alignment adj mark and substrate	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/08/22 16:17
S65	24	etch\$3 with SOI with alignment adj mark	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/08/22 16:40
S66	4	"6706610"	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/08/22 16:41

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S20	2044	alignment adj mark and etch\$4 with substrate	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/31 14:10
S21	324	alignment adj mark and etch\$4 with semiconductor with (oxide or nitride or dielectric or insulat\$4) with substrate	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/31 14:10
S22	123	alignment adj mark and etch\$4 with semiconductor with (oxide or nitride or dielectric or insulat\$4) with substrate same (expos\$3 with substrate)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/31 14:05
S23	33	S22 and stepper	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/31 14:06
S24	25	S22 and stepper and photoresist	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/31 14:06
S25	29	alignment adj mark and etch\$4 with SOI adj substrate	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/31 14:10

## EAST Search History

S26	16	S25 and alignment adj mark and etch\$4 with semiconductor with (oxide or nitride or dielectric or insulat\$4) with substrate	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2006/05/31 14:11
S27	16	S26 and (mask or photoresist or resist or photomask)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2006/05/31 14:11
S28	6	("5286673"   "5369050"   "6194287"   "6215197"   "6303460"   "6440816").PN.	US-PGPU B; USPAT; USOCR	OR	OFF	2006/05/31 14:39
S29	4	S28 and SOI	US-PGPU B; USPAT; USOCR	OR	OFF	2006/05/31 14:28
S30	9	deep adj alignment adj mark	US-PGPU B; USPAT; USOCR	OR	OFF	2006/05/31 14:30
S31	11	deep adj alignment adj mark	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/05/31 14:34
S32	1	S31 and SOI	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/05/31 14:30
S33	186	bulk adj substrate same (oxide or nitride or insulat\$3 or dielectric) same semiconductor adj layer	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/05/31 14:40

## EAST Search History

S34	3	S33 and alignment adj mark	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/05/31 14:37
S35	898	438/200.ccls.	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/05/31 14:37
S36	463	438/427.ccls.	US-PGPU B; USPAT; USOCR	OR	OFF	2006/05/31 14:39
S37	1748	438/424.ccls.	US-PGPU B; USPAT; USOCR	OR	OFF	2006/05/31 14:39
S38	138	438/405.ccls.	US-PGPU B; USPAT; USOCR	OR	OFF	2006/05/31 14:39
S39	769	438/462.ccls.	US-PGPU B; USPAT; USOCR	OR	OFF	2006/05/31 14:39
S40	391	438/975.ccls.	US-PGPU B; USPAT; USOCR	OR	OFF	2006/05/31 14:39
S41	704	257/797.ccls.	US-PGPU B; USPAT; USOCR	OR	OFF	2006/05/31 14:39
S42	8	S35 and alignment adj mark	US-PGPU B; USPAT; USOCR	OR	OFF	2006/05/31 14:39
S43	22	S36 and alignment adj mark	US-PGPU B; USPAT; USOCR	OR	OFF	2006/05/31 14:39
S44	34	S37 and alignment adj mark	US-PGPU B; USPAT; USOCR	OR	OFF	2006/05/31 14:39

## EAST Search History

S45	2	S38 and alignment adj mark	US-PGPU B; USPAT; USOCR	OR	OFF	2006/05/31 14:40
S46	145	S39 and alignment adj mark	US-PGPU B; USPAT; USOCR	OR	OFF	2006/05/31 14:40
S47	155	S40 and alignment adj mark	US-PGPU B; USPAT; USOCR	OR	OFF	2006/05/31 14:40
S48	276	S41 and alignment adj mark	US-PGPU B; USPAT; USOCR	OR	OFF	2006/05/31 14:40
S49	3	S42 and substrate same (oxide or nitride or insulat\$3 or dielectric) same semiconductor adj layer	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/05/31 14:40
S50	1	S43 and substrate same (oxide or nitride or insulat\$3 or dielectric) same semiconductor adj layer	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/05/31 14:40
S51	3	S44 and substrate same (oxide or nitride or insulat\$3 or dielectric) same semiconductor adj layer	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/05/31 14:41
S52	0	S45 and substrate same (oxide or nitride or insulat\$3 or dielectric) same semiconductor adj layer	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/05/31 14:41

## EAST Search History

S53	3	S46 and substrate same (oxide or nitride or insulat\$3 or dielectric) same semiconductor adj layer	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/05/31 14:41
S54	11	S47 and substrate same (oxide or nitride or insulat\$3 or dielectric) same semiconductor adj layer	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/05/31 14:41
S55	9	S48 and substrate same (oxide or nitride or insulat\$3 or dielectric) same semiconductor adj layer	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/05/31 14:41
S56	116	S48 and etch\$3 with substrate	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/05/31 14:41
S57	3	S49 and etch\$3 with substrate	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/05/31 14:42
S58	1	S50 and etch\$3 with substrate	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/05/31 14:41

## EAST Search History

S59	3	S51 and etch\$3 with substrate	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/05/31 14:42
S60	0	S52 and etch\$3 with substrate	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/05/31 14:42
S61	2	S53 and etch\$3 with substrate	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/05/31 14:42
S62	9	S54 and etch\$3 with substrate	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/05/31 14:50
S63	7	S55 and etch\$3 with substrate	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/05/31 14:43